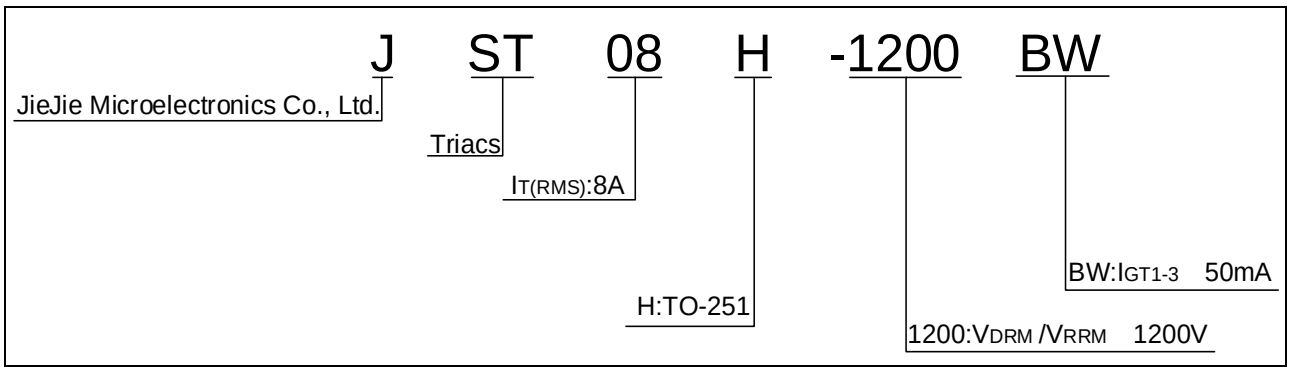
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	2.5	kV

(T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	50	mA
				90	
I_H	I_T =100mA		MAX.	50	mA
dV/dt	V_D=800V Gate Open T_j =125		MIN.	500	V/μs
(dI/dt)c	(dV/dt)c=20V/μs, T_j=125		MIN.	12	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	5	μs
t_{off}				50	

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =11A t_p=380μs	T_j=25	1.5	V
V_{TO}	Threshold voltage	T_j=125	0.82	V
R_D	Dynamic resistance	T_j=125	45	mΩ
I_{DRM}	V_D =V_{DRM} V_R =V_{RRM}	T_j=25	10	μA
I_{RRM}		T_j=125	1	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3	/W
$R_{th(j-a)}$	junction to ambient (AC)	100	/W


J
ST
08
H
-1200
BW
JieJie Microelectronics Co., Ltd.
Triacs
IT(RMS):8A
H:TO-251
1200:VDRM /VRRM 1200V
BW:IGT1-3 50mA

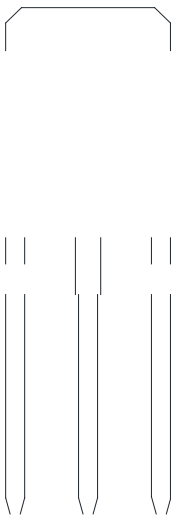


FIG.1: Maximum power dissipation versus RMS on-state current

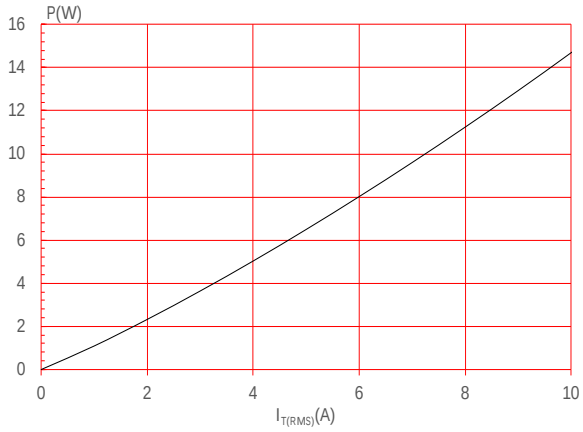


FIG.2: RMS on-state current versus case temperature

JST08H-1200BW

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